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Application No.: 10/645,642

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AMENDMENTS TO THE CLAIMS

Please amend claims 1, 3 and 6-9 and please cancel claim 12, such that the status of the claims is as follows:

1. (Currently Amended) A field effect transistor sandwiched organic semiconductor, comprising:
a substrate (1).

a gate electrode (2) formed on the surface of the substrate (1),

a gate insulation layer (3) formed on the substrate (1) and the gate ~~insulation layer~~
electrode (2),

which is characterized in that, further comprising:

an active layer (4) formed on the gate insulation layer (3), or meanwhile leaving a
part of the gate insulation layer (3) to be exposed,

a source and drain electrodes (5) formed on a part of the gate insulation layer (3) and
a part of the active layer (4),

an active layer (6) formed on the exposed part of the gate insulation layer (3), the
active layer (4), the source electrode and the drain electrode (5).

2. (Original) The field effect transistor according to claim 1, wherein the said active layer has holes.

3. (Currently Amended) The field effect transistor according to claim 2, wherein ~~the said a~~
semiconductor material is organic semiconductor material or ~~the a~~ hybridized product of organic
material and inorganic material.

4. (Original) The field effect transistor according to claim 3, wherein the said organic
semiconductor material is a solid-state material formed by mixing, eutecting or laminating of two
or more kinds of molecular material.

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5. (Original) The field effect transistor according to claim 4, wherein the said organic semiconductor material has a carrier mobility of at least $10^{-3} \text{cm}^2/\text{V.s.}$
6. (Currently Amended) The field effect transistor according to claim 1, wherein ~~the said a~~ semiconductor material for the active layer (4) is the same as that for the active layer (6).
7. (Currently Amended) The field effect transistor according to claim 1, wherein ~~the said a~~ semiconductor material for the active layer (4) is different from that for the active layer (6).
8. (Currently Amended) The field effect transistor according to claim 1, wherein ~~the said a~~ semiconductor material for the active layers (4) and (6) is eutectic.
9. (Currently Amended) The field effect transistor according to claim 1, wherein the said active layers (4) and (6) are comprised of at least one selected from a group consisting of CuPc, NiPc, ZnPc, H₂Pc, TiOPc, VOPc, F₁₆CuPc, F₁₆ZnPc and Pentacene, ~~respectively~~ respectively.
10. (Original) The field effect transistor according to claim 1, wherein the said active layer(4) is comprised of at least one selected from a group consisting of CuPc, NiPc, ZnPc, H₂Pc, F₁₆CuPc, F₁₆ZnPc and Pentacene, and the said active layer (6) is comprised of at least one selected from a group consisting of twin-Pc metal, H₂Nc, CoNc, CuNc, ZnNc and NiNc.
11. (Original) The field effect transistor according to claim 10, wherein the said twin-Pc metal is at least one selected from a group consisting of LaPc₂, CePc₂, PrPc₂, NdPc₂, SmPc₂, EuPc₂, GdPc₂, TbPc₂, DyPc₂, HoPc₂, ErPc₂, TmPc₂, YbPc₂, LuPc₂, YPc₂, ZrPc₂, HfPc₂ and SnPc₂.
12. (Canceled)